## **REMARKS**

Claims 17, 19 and 23 have been amended in order to more particularly point out, and distinctly claim the subject matter to which the applicants regard as their invention. It is believed that this Amendment is fully responsive to the Office Action datd September 22, 2004.

Claims 1 - 23 are currently pending in this patent application, claims 1, 16, 17 and 23 being independent claims.

At the outset, the applicant thanks the Examiner for indicating that claims 1 - 16 have been allowed.  $^{1/2}$ 

As to the merits of this case, the remaining claims 17 - 23 have been rejected as follows:

- (1) claims 17 21 stand rejected under 35 USC §103(a) based on <u>Kim</u> (U.S. Patent No. 6,664,573) in view of <u>Kusakabe</u> (U.S. Patent No. 5,569,942);
- (2) claim 22 stands rejected under 35 USC §103(a) based on <u>Kim</u> in view of <u>Kusakabe</u>, and further in view of <u>Matsuda</u> (U.S. Patent No. 6,525,347); and
  - (3) claim 23 stands rejected under 35 USC \$103(a) based on Kim in view of Kusakabe.

 $<sup>\</sup>frac{1}{2}$  See, item 5, page 5 of the outstanding Action.

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The applicants' claimed semiconductor light-receiving device, as now set forth in each of independent claims 17 and 23, clearly includes a unique and distinguishable claimed structural arrangement in which the high-concentration semiconductor intermediate tunneling layer allows electrons to go through this layer to the buffer layer by virtue of the tunnel effect, whereby the high-frequency response characteristics and the high-input saturation characteristics of the photodiode can be improved.

In contrast, the primary references <u>Kim</u> fails to teach or suggest a semiconductor intermediate layer "having a higher impurity concentration than the buffer layer," as acknowledged by the Examiner. <u>I/</u>

As to the secondary reference, <u>Kusakabe</u>, the intermediate layer 104 taught therein is <u>not</u> provided between the buffer layer and the light absorbing layer and is <u>not</u> the tunneling layer.

<u>Kusakabe</u> teaches a layer structure having the substrate 101, on which laminated are the buffer layer, the light absorbing layer 103, the intermediate layer 104, the multiplication layer 105 and the window layer 106 in this order. The applicants respectfully note and refer to the description of <u>Kusakabe</u> given in column 2, lines 8 - 15. The intermediate layer 104 of <u>Kusakabe</u> makes the

 $<sup>\</sup>frac{2l}{2}$  See, lines 8 - 11, page 2 of the outstanding Action.

discontinuity between the valence band. More particularly, <u>Kusakabe</u>'s Figure 4, the intermediate layer 104 accelerates holes moving towards the electrodes 113. The intermediate layer 104 does <u>not</u> employ the tunnel effect at all. This is also evidenced by the impurity concentration of the intermediate layer 104 taught by <u>Kusakabe</u>. <u>Kasukabe</u>'s intermediate layer 104 is as low as  $3x10^{15}$  to  $1x10^{16}$  cm<sup>-3</sup>. This allows the intermediate layer 104 to be sufficiently depleted with the electric field being applied in order to accelerate the movement of holes. <u>It is known by those skilled in the art that such a low concentration taught by Kusakabe does not bring about tunneling</u>.

In contrast, the high-impurity semiconductor intermediate tunneling layer has an impurity concentration, which is, for example, as high as  $2x10^{18}$  cm<sup>-3</sup>, as described in lines 21 and 22, page 10 of the applicants' specification, as originally filed. It is to be noted that the impurity concentration of the claimed invention is two digits higher than that of the intermediate layer 104 of <u>Kusakabe</u>.

Consequently, the claimed invention would not have been made by a person of ordinary skill in the art by applying the teachings of <u>Kusakabe</u> to those of <u>Kim</u>. As such, even if, arguendo, the teachings of <u>Kasukabe</u> can be combined with the teachings of <u>Kim</u>, such combined teachings would still fall far short in fully meeting the applicants' claimed invention, as now set forth in independent claim 17 (and claims 18 - 21, which depend therefrom) and independent

claim 23. Thus, a person of ordinary skill in the art would <u>not</u> have found the applicants' claimed invention obvious under 35 USC §103(a) based on <u>Kim</u> and <u>Kusakabe</u>, singly or in combination.

Accordingly, the withdrawal of the outstanding obviousness rejection under 35 USC §103(a) based on <u>Kim</u> (U.S. Patent No. 6,664,573) in view of <u>Kusakabe</u> (U.S. Patent No. 5,569,942) is in order, and is therefore respectfully solicited.

As to the other secondary reference of <u>Matsuda</u>, such reference is narrowly relied upon for teaching "a semiconductor optical waveguide path that is formed on the semi-insulating substrate and guides light to the light absorption layer." However, such teachings of <u>Matsuda</u> does <u>not</u> supplement the above-discussed deficiencies in the teachings of <u>Kim</u> and <u>Kasukabe</u> in failing to teach the claimed invention, as now set forth in claim 17 from which claim 22 depends.

Accordingly, the withdrawal of the outstanding obviousness rejection under 35 USC §103(a) based on <u>Kim</u> in view of <u>Kusakabe</u>, and further in view of <u>Matsuda</u> (U.S. Patent No. 6,525,347) is in order, and is therefore respectfully solicited.

In view of the aforementioned amendments and accompanying remarks, claims, as

amended, are in condition for allowance, which action, at an early date, is requested.

If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact the applicants' undersigned attorney at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

In the event that this paper is not timely filed, the applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper to Deposit Account No. 01-2340.

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 $<sup>\</sup>frac{3!}{2}$  See, lines 1 and 2, page 4 of the outstanding Action.